

Photocouplers GaAlAs Infrared LED & Photo IC

TLP2766F

1. Applications

- · Factory Networking
- · High-Speed Digital Interfacing for Instrumentation and Control Devices
- · Plasma Display Panels (PDPs)

2. General

The Toshiba TLP2766F consists of a high-output GaAlAs light-emitting diode coupled with a high-speed photo-diode-transistor chip. The TLP2766 guarantees operation at up to 125 °C and on supplies from 2.7 V to 5.5 V. It is offered in the SDIP6 package. The TLP2766 has an internal Faraday shield that provides a guaranteed common-mode transient immunity of ± 20 kV/ μ s.

3. Features

- (1) Inverter logic type (Totem pole output)
- (2) Package: SDIP6
- (3) Operating temperature: -40 to 125 °C
- (4) Supply voltage: 2.7 to 5.5 V
- (5) Data transfer rate: 20 MBd (typ.) (NRZ)
- (6) Threshold input current: 3.5 mA (max)
- (7) Supply current: 3 mA (max)
- (8) Common-mode transient immunity: ±20 kV/µs (min)
- (9) Isolation voltage: 5000 Vrms (min)
- (10) Safety standards

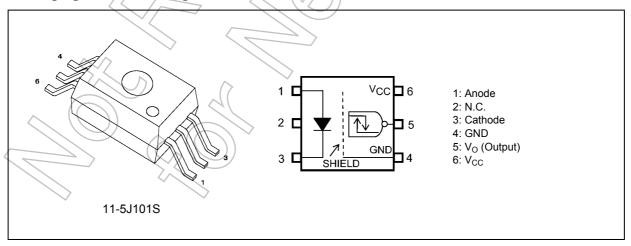
UL-approved: UL1577, File No.E67349

cUL-approved: CSA Component Acceptance Service No.5A File No.E67349

VDE-approved: EN60747-5-5 (Note 1)

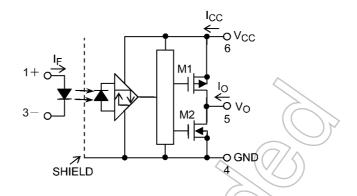
Note 1: When an EN60747-5-5 approved type is needed, please designate the Option (D4).

4. Packaging and Pin Configuration





5. Internal Circuit (Note)



Note: A $0.1\mu F$ bypass capacitor must be connected between pin 6 and pin 4.

6. Principle of Operation

6.1. Truth Table

Input	LED	M1	M2	Output
Н	ON	OFF	ON	
L	OFF	ON	OFF <	(H)

6.2. Mechanical Parameters

Characteristics	10.16-mm Pitch TLP2766F	Unit
Creepage distances	8.0 (min)	mm
Clearance distances	8.0 (min)	
Internal isolation thickness	0.4 (min)	





7. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

	Characteristics		Symbol	Note	Rating	Unit
LED	Input forward current		I _F		25	mA
	Input forward current derating	(T _a ≥ 110 °C)	$\Delta I_F/\Delta T_a$		-0.67	mA/°C
	Input forward current (pulsed)		I _{FP}	(Note 1)	40	mA
	Input forward current derating (pulsed)	(T _a ≥ 110 °C)	$\Delta I_{FP}/\Delta T_a$		-1.0	mA/°C
	Input power dissipation		P _D		40	mW
	Input power dissipation derating	(T _a ≥ 110 °C)	$\Delta P_D/\Delta T_a$	(7/	-1.0	mW/°C
	Input reverse voltage		V _R	1/5	5	V
Detector	Output current		I ₀ ((10	mA
	Output voltage		Vo		6	V
	Supply voltage		Vcc		6	
	Output power dissipation		Po		60	mW
	Output power dissipation derating	(T _a ≥ 110 °C)	$\Delta P_0/\Delta T_a$	^	-1.5	mW/°C
Common	Operating temperature		Topr		-40 to 125	°C
	Storage temperature		T _{stg}		-55 to 150	
	Lead soldering temperature	(10 s)	T _{sol}	C	260	
	Isolation voltage	AC, 60 s, R.H. ≤ 60 %	BV _S	(Note 2)	5000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 1: Pulse width (PW) \leq 1 ms, duty = 50 %

Note 2: This device is considered as a two-terminal device: Pins 1, 2 and 3 are shorted together, and pins 4, 5 and 6 are shorted together.

8. Recommended Operating Conditions (Note)

Characteristics	Symbol	Note	Min	Тур.	Max	Unit
Input on-state current	I _{F(ON)}	(Note 1)	4.5	_	15	mA
Input off-state voltage	V _{F(OFF)}		0	_	0.8	V
Supply voltage	V _{CC}	(Note 2)	2.7	3.3/5.0	5.5	
Operating temperature	T _{opr}	(Note 2)	-40	_	125	°C

Note: The recommended operating conditions are given as a design guide necessary to obtain the intended performance of the device. Each parameter is an independent value. When creating a system design using this device, the electrical characteristics specified in this datasheet should also be considered.

Note: A ceramic capacitor (0.1 μF) should be connected between pin 6 and pin 4 to stabilize the operation of a highgain linear amplifier. Otherwise, this photocoupler may not switch properly. The bypass capacitor should be placed within 1 cm of each pin.

Note 1: The rise and fall times of the input on-current should be less than 0.5 μ s.

Note 2: Denotes the operating range, not the recommended operating condition.



9. Electrical Characteristics (Note) (Unless otherwise specified, T_a = -40 to 125 °C, V_{CC} = 2.7 to 5.5 V)

Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Input forward voltage	V_{F}	_	I _F = 10 mA, T _a = 25 °C	1.45	1.55	1.7	V
Input forward voltage temperature coefficient	$\Delta V_F/\Delta T_a$	_	I _F = 10 mA		-2.0	_	mV/°C
Input reverse current	I _R		V _R = 5 V, T _a = 25 °C			10	μА
Input capacitance	Ct	-	V = 0 V, f = 1 MHz, T _a = 25 °C		60	_	pF
Low-level output voltage	V _{OL}	Fig. 12.1.1	I _F = 14 mA, I _O = 4 mA	75	_	0.4	V
High-level output voltage	V _{OH}	Fig. 12.1.2	V _F = 1.05 V, I _O = -4 mA, V _{CC} = 3.3 V	2.3	_	_	
			V _F = 1.05 V, I _O = -4 mA, V _{CC} = 5 V	4	_	_	
Low-level supply current	I _{CCL}	Fig. 12.1.3	I _F = 14 mA	_	1.6	3	mA
High-level supply current	I _{CCH}	Fig. 12.1.4	I _F = 0 mA	, -(1.5	> 3	
Threshold input current (H/L)	I _{FHL}	_	$I_0 = 1.6 \text{ mA}, V_0 < 0.4 \text{ V}$	4	(0,9)	3.5	

Note: All typical values are at $T_a = 25$ °C.

10. Isolation Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Note	Test Conditions	Min	Тур.	Max	Unit
Total capacitance (input to output)	C _S	(Note 1)	V _S = 0 V, f = 1 MHz	_	0.8		pF
Isolation resistance	Rs	(Note 1)	V _S = 500 V, R.H. ≤ 60 %	1 × 10 ¹²	1014		Ω
Isolation voltage	BVs	(Note 1)	AC, 60 s	5000			Vrms
			AC, 1 s in oil	_	10000	_	
))	DC, 60 s in oil	_	10000		Vdc

Note 1: This device is considered as a two-terminal device: Pins 1, 2 and 3 are shorted together, and pins 4, 5 and 6 are shorted together.





11. Switching Characteristics (Note)

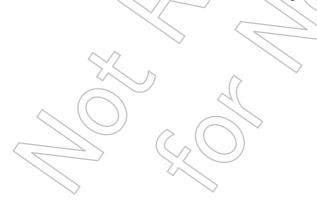
11.1. Switching Characteristics (1) (Unless otherwise specified, T_a = -40 to 125 °C, V_{CC} = 2.7 to 3.6 V)

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Propagation delay time (H/L)	t _{pHL}	(Note 1)	Fig. 12.1.5	I_F = 0 \rightarrow 14 mA, R_{IN} = 100 Ω , C_L = 15 pF		28	40	ns
Propagation delay time (L/H)	t _{pLH}	(Note 1)		I_F = 14 \rightarrow 0 mA, R_{IN} = 100 Ω , C_L = 15 pF		25	40	
Pulse width distortion	t _{pHL} -	(Note 1)		I_F = 14 mA, R_{IN} = 100 Ω , C_L = 15 pF	Z5)	3	25	
Propagation delay skew (device to device)	t _{psk}	(Note 1), (Note 2)			30		30	
Propagation delay time (H/L)	t _{pHL}	(Note 1)	Fig. 12.1.5	I_F = 0 \rightarrow 6 mA, R_{IN} = 100 Ω , C_L = 15 pF	_	34	55	
Propagation delay time (L/H)	t _{pLH}	(Note 1)		I_F = 6 \rightarrow 0 mA, R_{IN} = 100 Ω ; C_L = 15 pF	-	25	55	
Pulse width distortion	t _{pHL} - t _{pLH}	(Note 1)		$I_F = 6 \text{ mA}, R_{IN} = 100 \Omega,$ $C_L = 15 \text{ pF}$, -(9	30	
Propagation delay skew (device to device)	t _{psk}	(Note 1), (Note 2)			-30		30	
Fall time	t _f	(Note 1)	Fig. 12.1.5	$\begin{aligned} I_F &= 0 \rightarrow 14 \text{ mA, R}_{IN} = 100 \ \Omega, \\ C_L &= 15 \text{ pF} \end{aligned}$		15		
Rise time	t _r	(Note 1)		I_F = 14 \rightarrow 0 mA, R_{IN} = 100 Ω , C_L = 15 pF		15	_	
Common-mode transient immunity at output high	CM _H		Fig. 12.1.6	$V_{CM} = 1000 V_{p,p}, I_F = 0 \text{ mA},$ $V_{O(min)} = 2 V, V_{CC} = 3.3 V,$ $T_a = 25 ^{\circ}C$	±20	±25	_	kV/μs
Common-mode transient immunity at output low	CM _L			$V_{CM} = 1000 V_{p-p}, I_F = 14 \text{ mA}, V_{O(max)} = 0.4 \text{ V}, V_{CC} = 3.3 \text{ V}, T_a = 25 ^{\circ}\text{C}$	±20	±25	_	

Note: All typical values are at T_a = 25 °C.

Note 1: f = 5 MHz, duty = 50 %, input current $t_r = t_f = 5$ ns, C_L is approximately 15 pF which includes probe and stray wiring capacitance.

Note 2: The propagation delay skew, t_{psk}, is equal to the magnitude of the worst-case difference in t_{pHL} and/or t_{pLH} that will be seen between units at the same given conditions (supply voltage, input current, temperature, etc).



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11.2. Switching Characteristics (2) (Unless otherwise specified, T_a = -40 to 125 °C, V_{CC} = 4.5 to 5.5 V)

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Propagation delay time (H/L)	t _{pHL}	(Note 1)	Fig. 12.1.5	I_F = 0 \rightarrow 14 mA, R_{IN} = 100 Ω , C_L = 15 pF	_ <	30	45	ns
Propagation delay time (L/H)	t _{pLH}	(Note 1)		I_F = 14 \rightarrow 0 mA, R_{IN} = 100 Ω , C_L = 15 pF		24	45	
Pulse width distortion	t _{pHL} -	(Note 1)		I_F = 14 mA, R_{IN} = 100 Ω, C_L = 15 pF		9	25	
Propagation delay skew (device to device)	t _{psk}	(Note 1), (Note 2)			-30		30	
Propagation delay time (H/L)	t _{pHL}	(Note 1)	Fig. 12.1.5	$\begin{aligned} I_F &= 0 \rightarrow 6 \text{ mA, } R_{IN} = 100 \ \Omega, \\ C_L &= 15 \text{ pF} \end{aligned}$		38	55	
Propagation delay time (L/H)	t _{pLH}	(Note 1)		I_F = 6 \rightarrow 0 mA, R_{IN} = 100 Ω , C_L = 15 pF	_	28	55	
Pulse width distortion	t _{pHL} - t _{pLH}	(Note 1)		$I_F = 6 \text{ mA}, R_{IN} = 100 \Omega,$ $C_L = 15 \text{ pF}$	-	10	30	
Propagation delay skew (device to device)	t _{psk}	(Note 1), (Note 2)			-30		30	
Fall time	t _f	(Note 1)	Fig. 12.1.5	$I_F = 0 \rightarrow 14 \text{ mA}, R_{IN} = 100 \Omega,$ $C_L = 15 \text{ pF}$		15/	_	
Rise time	t _r	(Note 1)		$I_F = 14 \rightarrow 0$ mA, $R_{IN} = 100 \Omega$, $C_L = 15$ pF	\mathcal{D}	15	_	
Common-mode transient immunity at output high	CM _H		Fig. 12,1.6	$V_{CM} = 1000 V_{p-p}, I_F = 0 \text{ mA}, V_{O(min)} = 4 V, V_{CC} = 5 V, T_a = 25 °C$)±20	±25	_	kV/μs
Common-mode transient immunity at output low	CM _L	(($V_{CM} = 1000 \text{ V}_{\text{p-p}}, \text{ I}_{\text{F}} = 14 \text{ mA}, \\ V_{O(\text{max})} = 0.4 \text{ V}, \text{ V}_{CC} = 5 \text{ V}, \\ T_{a} = 25 ^{\circ}\text{C}$	±20	±25	_	

Note: All typical values are at $T_a = 25$ °C.

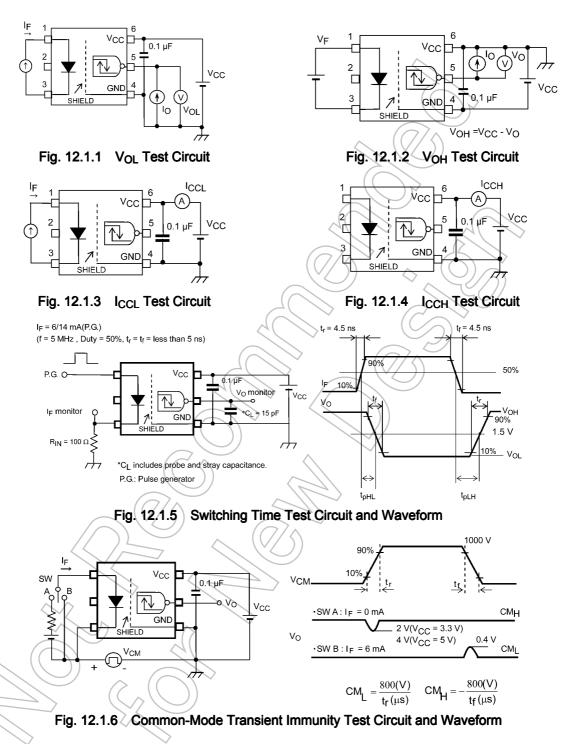
Note 1: f = 5 MHz, duty = 50 %, input current $t_r = t_f = 5$ ns, C_L is approximately 15 pF which includes probe and stray wiring capacitance.

Note 2: The propagation delay skew, t_{psk}, is equal to the magnitude of the worst-case difference in t_{pHL} and/or t_{pLH} that will be seen between units at the same given conditions (supply voltage, input current, temperature, etc).



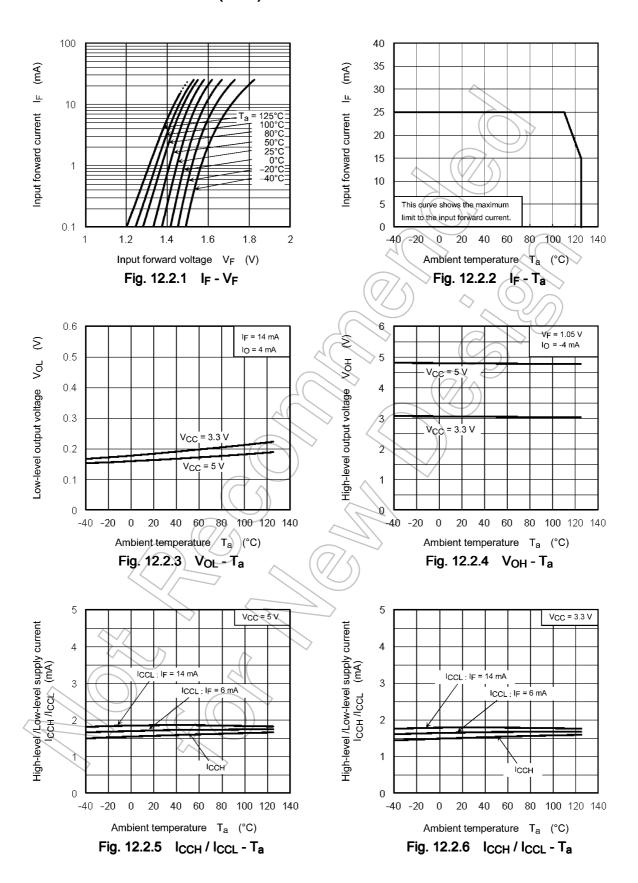
12. Test Circuits and Characteristics Curves

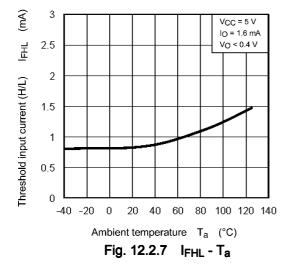
12.1. Test Circuits

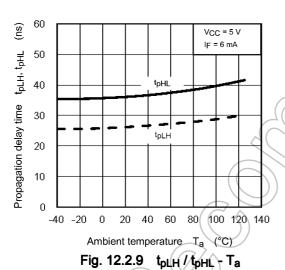


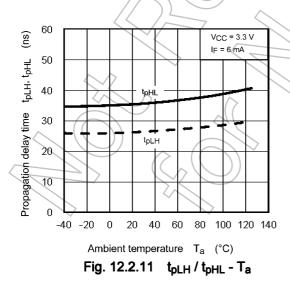


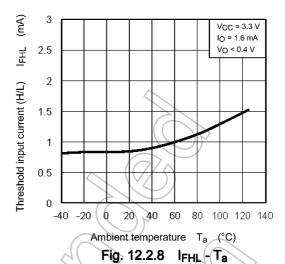
12.2. Characteristics Curves (Note)

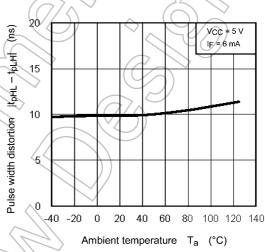














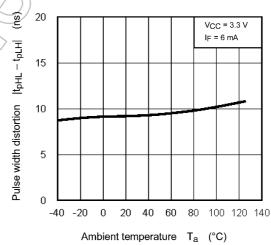
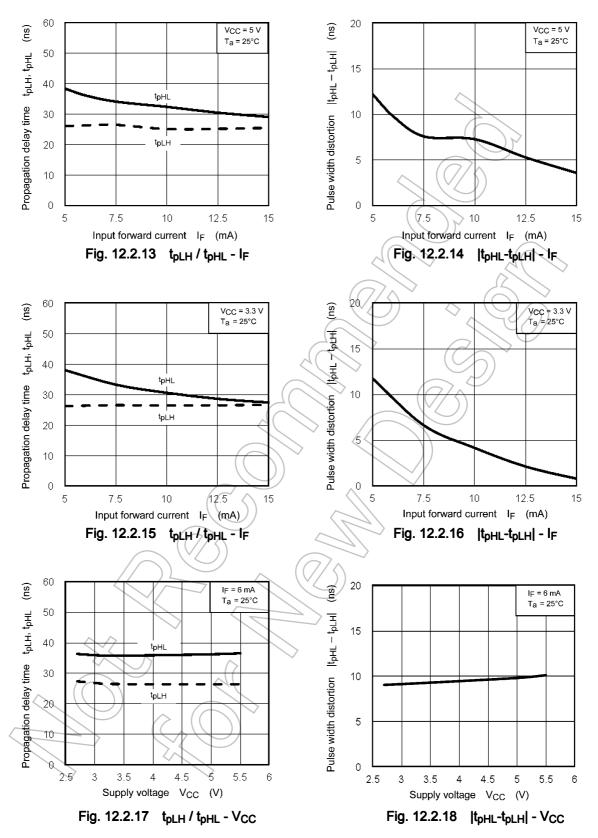


Fig. 12.2.12 $|t_{pHL}-t_{pLH}|$ - T_a

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NOTE: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



13. Soldering and Storage

13.1. Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

· When using soldering reflow.

The soldering temperature profile is based on the package surface temperature. (See the figure shown below, which is based on the package surface temperature.) Reflow soldering must be performed once or twice.

The mounting should be completed with the interval from the first to the last mountings being 2 weeks.

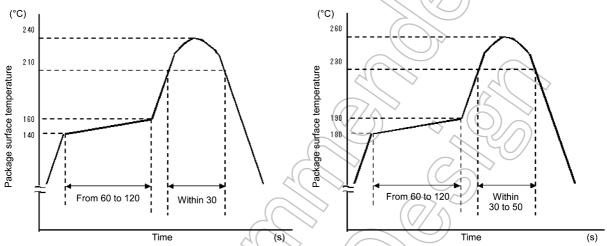


Fig. 13.1.1 An Example of a Temperature Profile When Sn-Pb Eutectic Solder Is Used

Fig. 13.1.2 An Example of a Temperature Profile When Lead(Pb)-Free Solder Is Used

- When using soldering flow (Applicable to both eutectic solder and Lead(Pb)-Free solder)
 Preheat the device at a temperature of 150 °C (package surface temperature) for 60 to 120 seconds.
 Mounting condition of 260 °C within 10 seconds is recommended.
 Flow soldering must be performed once.
- When using soldering Iron (Applicable to both eutectic solder and Lead(Pb)-Free solder)
 Complete soldering within 10 seconds for lead temperature not exceeding 260°C or within 3 seconds not exceeding 350°C

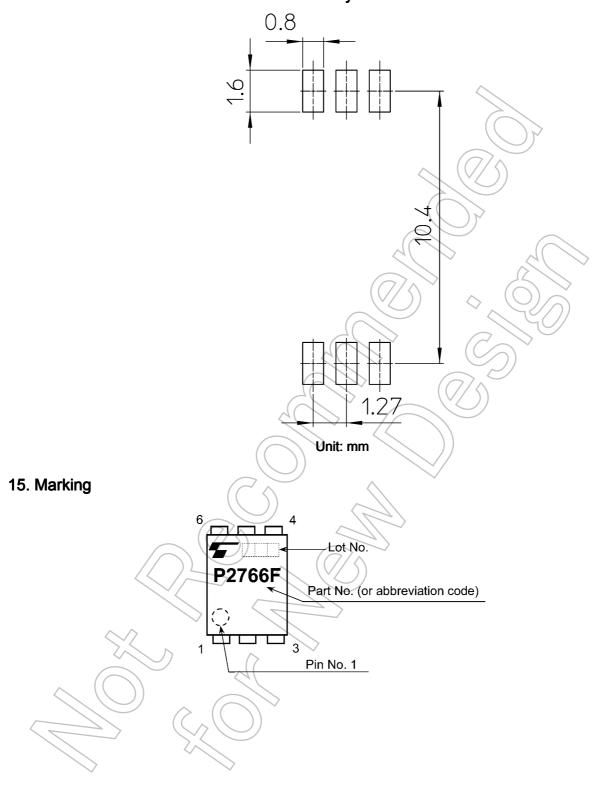
Heating by soldering iron must be done only once per lead.

13.2. Precautions for General Storage

- · Avoid storage locations where devices may be exposed to moisture or direct sunlight.
- · Follow the precautions printed on the packing label of the device for transportation and storage.
- Keep the storage location temperature and humidity within a range of 5 °C to 35 °C and 45 % to 75 %, respectively.
- Do not store the products in locations with poisonous gases (especially corrosive gases) or in dusty conditions.
- Store the products in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
- · When restoring devices after removal from their packing, use anti-static containers.
- · Do not allow loads to be applied directly to devices while they are in storage.
- If devices have been stored for more than two years under normal storage conditions, it is recommended that you check the leads for ease of soldering prior to use.



14. Land Pattern Dimensions for Reference Only



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16. EN60747-5-5 Option (D4) Specification

• Part number: TLP2766F (Note 1)

• The following part naming conventions are used for the devices that have been qualified according to option (D4) of EN60747.

Example: TLP2766F(D4-TP, F)

D4: EN60747 option

TP: Tape type

F: [[G]]/RoHS COMPATIBLE (Note 2)

Note 1: Use TOSHIBA standard type number for safety standard application.

e.g., TLP2766F(D4-TP,F) \rightarrow TLP2766F

Note 2: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.

RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronics equipment.

Description		Symbol	Rating	Unit
Application classification for rated mains voltage ≤ 300 Vrms for rated mains voltage ≤ 600 Vrms			I-IV I-III	_
Climatic classification		(//5)	40 / 125 / 21	_
Pollution degree			2	_
	TLPxxx type		890	Vpeak
Maximum operating insulation voltage	TLPxxxF type	VIORM	1140	
Input to output test voltage, Method A	TLPxxx type	V	1424	Vnook
V_{pr} = 1.6 × V_{IORM} , type and sample test t_p = 10 s, partial discharge < 5 pC	TLPxxxF type	V _{pr}	1824	- Vpeak
Input to output test voltage, Method B V _{pr} = 1.875 × V _{IORM} , 100 % production test	TLPxxx type	V	1670	Vnoak
t _p = 1 s, partial discharge < 5 pC	TLPxxxF type	V _{pr}	2140	Vpeak
Highest permissible overvoltage (transient overvoltage, t _{pr} = 60 s)		V _{TR}	8000	Vpeak
Safety limiting values (max. permissible ratings in case of also refer to thermal derating current (input current I_{F} , $P_{so} = 0$) power (output or total power dissipation) temperature		I _{si} P _{so} T _s	300 700 150	mA mW °C
Insulation resistance V_{IO} = 500 V, T_a = 25 °C V_{IO} = 500 V, T_a = 100 °C V_{IO} = 500 V, T_a = T_s	;	R _{si}		Ω

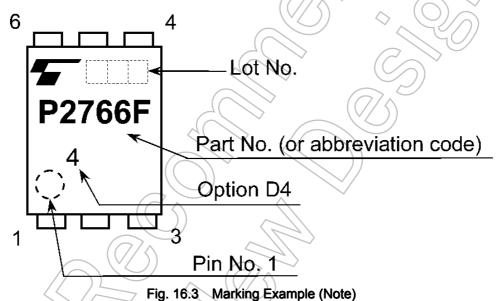
Fig. 16.1 EN60747 Isolation Characteristics



		7.62-mm pitch TLPxxx type	10.16-mm pitch TLPxxxF type
Minimum creepage distance	Cr	7.0 mm	8.0 mm
Minimum clearance	CI	7.0 mm	8.0 mm
Minimum insulation thickness	ti	0,4 mm	
Comparative tracking index	СТІ	175	

Fig. 16.2 Insulation Related Specifications (Note)

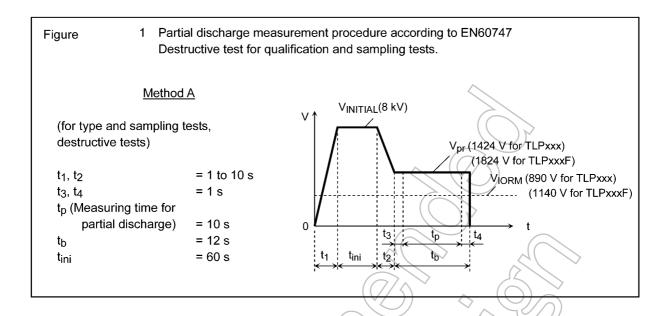
Note: This photocoupler is suitable for **safe electrical isolation** only within the safety limit data. Maintenance of the safety data shall be ensured by means of protective circuits.

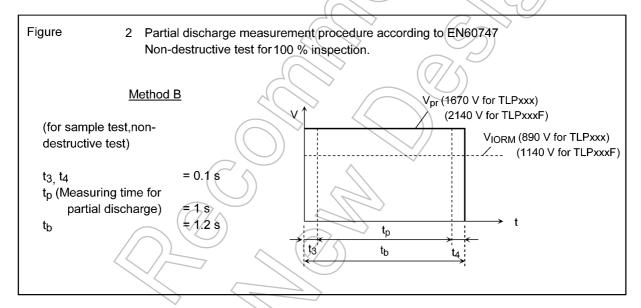


rig. 10.5 Walking Example (Note)

Note: The above marking is applied to the photocouplers that have been qualified according to option (D4) of EN60747.







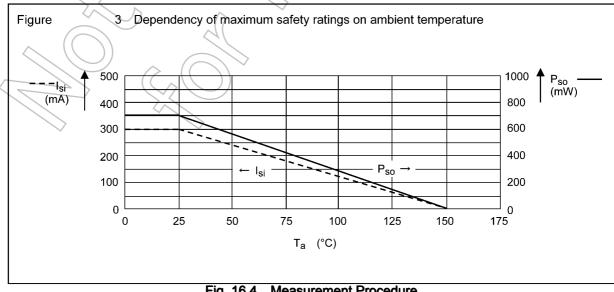
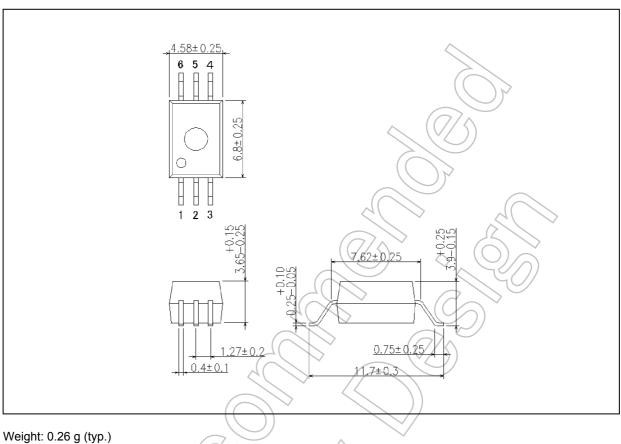


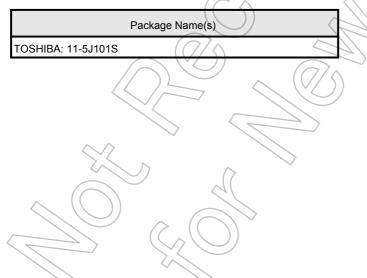
Fig. 16.4 **Measurement Procedure**



Package Dimensions

Unit: mm







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- GaAs (Gallium Arsenide) is used in Product. GaAs is harmful to humans if consumed or absorbed, whether in the form of dust or vapor.
 Handle with care and do not break, cut, crush, grind, dissolve chemically or otherwise expose GaAs in Product.
- Do not use or otherwise make available Product or related software or technology for any military purposes, including without limitation, for the design, development, use, stockpiling or manufacturing of nuclear, chemical, or biological weapons or missile technology products (mass destruction weapons). Product and related software and technology may be controlled under the applicable export laws and regulations including, without limitation, the Japanese Foreign Exchange and Foreign Trade Law and the U.S. Export Administration Regulations. Export and re-export of Product or related software or technology are strictly prohibited except in compliance with all applicable export laws and regulations.
- Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.
 Please use Product in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. TOSHIBA ASSUMES NO LIABILITY FOR DAMAGES OR LOSSES OCCURRING AS A RESULT OF NONCOMPLIANCE WITH APPLICABLE LAWS AND REGULATIONS.

单击下面可查看定价,库存,交付和生命周期等信息

>>Toshiba(东芝)